



PATENT ABSTRACTS OF JAPAN

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(54) INSULATED-GATE SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

source electrode 32 and the polysilicon electrode 37 are separated from each other by the insulating film 31.

(57) Abstract:

PROBLEM TO BE SOLVED: To prevent a short circuit between a source electrode and an EQR aluminum electrode in a temperature cycle test, by forming an EQR polysilicon electrode between the upside of a field oxide film and the underside of a layer insulating film.

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SOLUTION: Since an EQR polysilicon electrode 37 is formed on a field oxide film 36, an EQR effect is enhanced, and the peripheral of the chip is shortened by shortening the length of the EQR, and the chip area is reduced. Since an EQR aluminum electrode 38 connects the polysilicon electrode 37 with a high-concentration one conductivity impurity region electrically, a clearance from a source electrode 32 can be made larger. Besides, a short circuit between the source electrode 32 and the aluminum electrode 38 by an aluminum slide phenomenon generated in temperature cycle test is prevented, since the polysilicon electrode 37 is formed under a layer insulating film 31, and the

